Federal Agency on Technical Regulating and Metrology

(Rostekhregulirovanie)

CENTER FOR SURFACE AND VACUUM RESEARCH

Diffusion Length Measurement System of Minority Charge Carriers in Silicon Wafers

Quality control of initial silicon wafers by measurements of diffusion length of minority charge carriers and iron contamination, using a contactless, real-time surface photovoltage method.

Specifications

Measuring range:

Diffusion Length (L_D)	10 µm to 2000 µm or $L_D < t$ (t is the wafer thickness)
Iron concentration	$10^9 \div 10^{13}$ cm^{-3}
Accuracy of measurements	15 ÷ 30 %

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